

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	bruley near john.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:41
2	BRS	L2	19	kane near terence.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:42
3	BRS	L3	7	tenney near michael.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	0	(mosfet) near15 (defective near feature\$1)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:44
5	BRS	L5	113	(mosfet) near15 (defective)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:45
6	BRS	L6	4	((site-specific or site near specific)) near (junction)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:47

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	4	((specific-site or site near specific)) near (junction)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:47
8	BRS	L8	12	(cap near layer) near25 (defective)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:48
9	BRS	L9	151	(cap near layer) near25 (defect\$4)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:48

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	1591	(cap) near25 (defect\$4)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:48
11	BRS	L11	139	((cap) near25 (defect\$4)) near35 ((opening or hole or aperture or recess))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:52
12	BRS	L12	28951	(defect\$4) near35 ((opening or hole or aperture or recess or via))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	30	(defect\$4 near feature\$1) near35 ((opening or hole or aperture or recess or via))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:54
14	BRS	L14	20	(defect\$4) near35 ((opening or hole or aperture or recess or via)) near25 (mosfet)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:59
15	BRS	L15	54405	(remov\$3 near5 cap)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:59

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	2114	(remov\$3) near5 (cap near3 layer\$1)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 15:59
17	BRS	L17	3	(remov\$3) near5 (cap near3 layer\$1) near25 (defective)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:00
18	BRS	L18	10	(remov\$3) near5 (cap near3 layer\$1) near25 (specific)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	15	(etch\$3) near5 (cap near3 layer\$1) near25 (specific)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:04

	U	1	Document ID	Title	Current OR
1	X		US 20030207517 A1	Flash memory cell and method for fabricating a flash	438/200
2	X		US 20030032273 A1	Flash memory cell and method for fabricating a flash memory cell	438/594
3			US 6717224 B2	Flash memory cell and method for fabricating a flash	257/396
4			US 6576537 B2	Flash memory cell and method for fabricating a flash memory cell	438/594
5			US 5427965 A	Method of fabricating a complementary heterojunction FET	438/169
6			US 5349214 A	Complementary heterojunction device	257/192
7			JP 05286304 A	PNEUMATIC RADIAL TIRE	

	U	1	Document ID	Title	Current OR
8	X		US 20040087161 A	Code implantation method for mask read only memory, involves forming resist layer with line/space pattern extending in specific direction, on dielectric and cap layers, and removing cap layer portion uncovered by resist layer	
9	X		US 6649533 B	Semiconductor device manufacturing method involves forming under bump metal layer on contact pad area of substrate without leaving vacuum environment after removing cap and insulating layer from specific portion of pad area	
10	X		US 6060746 A	Power transistor fabrication for switching application, involves forming N-type drain and source electrodes in pillars provided adjacent to dielectric and N-type arsenic doped silicate layers, respectively	

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1400	(analyz\$3) near15 (defective)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:21
2	BRS	L2	1	(analyz\$3) near15 (defective near feature\$1)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:21
3	BRS	L3	170	(analyz\$3) near15 (defective) near15 (imag\$4)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 16:22